

# isc Silicon NPN Power Transistors

# MJ15024G

### **DESCRIPTION**

- Complement to Type PNP MJ15025
- Excellent Safe Operating Area
- High DC current Gain
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**

 Designed for high power audio, disk head positioners and other linear applications

# PIN 1.Base 2.Emitter 3.Collestor(case) TO-3 Package

# ABSOLUTE MAXIMUM RATINGS(Tc=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	400	٧
V <sub>CEO</sub>	Collector-Emitter Voltage	250	V
V <sub>EBO</sub>	Emitter-Base Voltage	mitter-Base Voltage 5	
Ic	Collector Current-Continuous	16	Α
I <sub>CM</sub> (1)	Collector Current-Peak 30		Α
I <sub>B</sub>	Base Current-Continuous	5	Α
P <sub>D</sub>	Total Power Dissipation @T <sub>C</sub> =25℃ 250		W
Tj	Junction Temperature -65~200		$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-65~200	$^{\circ}$

# mm DIM MIN MAX A 25.30 | 26.67 8.50 D 0.90 1.10 1.40 1,60 G Н 5.46 11.30 13.50 K 16.75 17.05 19.62 N 19.40 U 30.00 4.30

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	0.70	°C/W

<sup>(1)</sup> Pulse Test: Pulse Width = 5 ms, Duty Cycle< 10%.



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### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 100mA ;I <sub>B</sub> = 0	250		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 0.8A		1.4	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	Ic= 16A; I <sub>B</sub> = 3.2A		4.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 8A ; V <sub>CE</sub> = 4V		2.2	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 200V; I <sub>B</sub> = 0		0.5	mA
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 250V; I <sub>E</sub> = 0		0.25	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> =0		0.5	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 8A ; V <sub>CE</sub> = 4V	15	60	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 16A; V <sub>CE</sub> = 4V	5		
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz	300		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 10V; f <sub>test</sub> = 1.0MHz	4		MHz

<sup>(1)</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle < 2%.

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